



High-end Power Semiconductor Manufacturer

## ZP320A 2000-2800V Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current		$I_{FAV}$		320 A	
Repetitive peak reverse voltage		$V_{RRM}$		2000 – 2800 V	
$V_{RRM}, V$	2000	2200	2400	2600	2800
Voltage code	20	22	24	26	28
$T_j, ^\circ C$	-60 – 175				

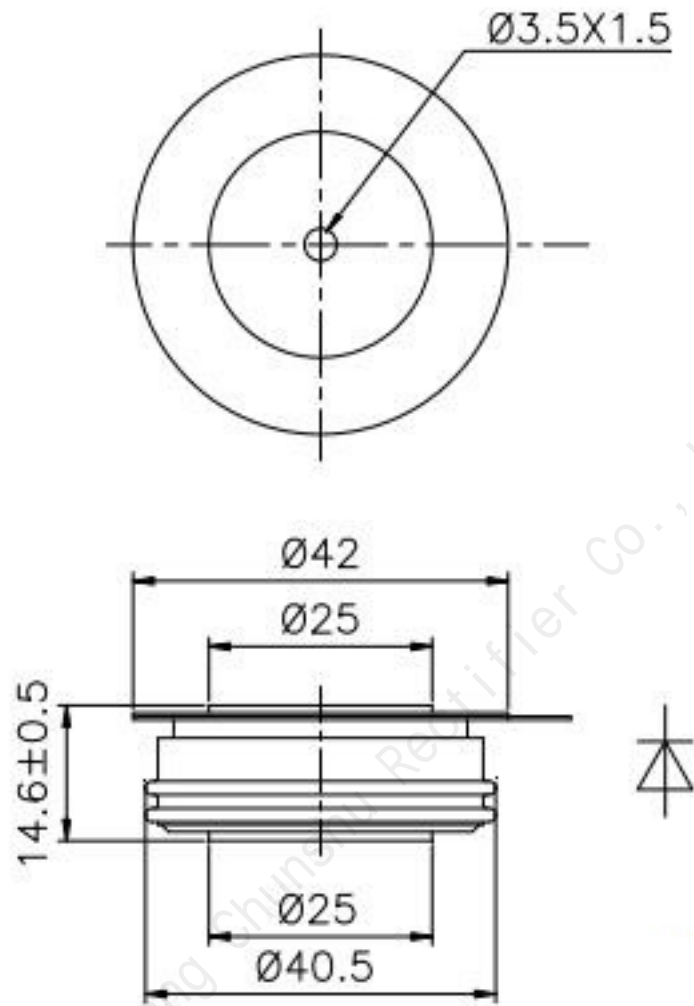
### MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
<b>ON-STATE</b>					
$I_{FAV}$	Average forward current	A	320	$T_c=100\text{ }^\circ C$ ; Double side cooled; 180° half-sine wave; 50 Hz	
$I_{FRMS}$	RMS forward current	A	502	$T_c=135\text{ }^\circ C$ ; Double side cooled; 180° half-sine wave; 50 Hz	
$I_{FSM}$	Surge forward current	kA	5.5 6.3	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$	180° half-sine wave; 50 Hz ( $t_p=10\text{ ms}$ ); single pulse; $V_R=0\text{ V}$ ;
			6.0 6.9	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$	180° half-sine wave; 60 Hz ( $t_p=8.3\text{ ms}$ ); single pulse; $V_R=0\text{ V}$ ;
$I^2t$	Safety factor	$A^2s\cdot 10^3$	150 195	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$	180° half-sine wave; 50 Hz ( $t_p=10\text{ ms}$ ); single pulse; $V_R=0\text{ V}$ ;
			145 195	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$	180° half-sine wave; 60 Hz ( $t_p=8.3\text{ ms}$ ); single pulse; $V_R=0\text{ V}$ ;
<b>BLOCKING</b>					
$V_{RRM}$	Repetitive peak reverse voltages	V	2000–2800	$T_{j\min} < T_j < T_{j\max}$ ; 180° half-sine wave; 50 Hz;	
$V_{RSM}$	Non-repetitive peak reverse voltages	V	2100–2900	$T_{j\min} < T_j < T_{j\max}$ ; 180° half-sine wave; 50 Hz; single pulse;	
$V_R$	Reverse continuous voltages	V	$0.75\cdot V_{RRM}$	$T_j=T_{j\max}$ ;	
<b>THERMAL</b>					
$T_{stg}$	Storage temperature	$^\circ C$	-60–175		
$T_j$	Operating junction temperature	$^\circ C$	-60–175		
<b>MECHANICAL</b>					
F	Mounting force	kN	5.0–7.0		
a	Acceleration	$m/s^2$	50	Device unclamped	
			100	Device clamped	

## CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
<b>ON-STATE</b>					
$V_{FM}$	Peak forward voltage, max	V	2.01	$T_j=25\text{ }^\circ\text{C}; I_{FM}=1005\text{ A}$	
$V_{F(TO)}$	Forward threshold voltage, max	V	1.01	$T_j=T_{j\text{ max}}$	
$r_T$	Forward slope resistance, max	m $\Omega$	1.010	$0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$	
<b>BLOCKING</b>					
$I_{RRM}$	Repetitive peak reverse current, max	mA	35	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$	
<b>THERMAL</b>					
$R_{thjc}$	Thermal resistance, junction to case, max	$^\circ\text{C/W}$	0.070	Direct current	Double side cooled
$R_{thjc-A}$			0.154		Anode side cooled
$R_{thjc-K}$			0.126		Cathode side cooled
$R_{thck}$	Thermal resistance, case to heatsink, max	$^\circ\text{C/W}$	0.010	Direct current	
<b>MECHANICAL</b>					
w	Weight, typ	g	65		
$D_s$	Surface creepage distance	mm (inch)	11.74 (0.462)		
$D_a$	Air strike distance	mm (inch)	11.60 (0.457)		

OVERALL DIMENSIONS



ZT30

All dimensions in millimeters